

Si_l(ref)

Si_l(Si)

REFERENCE STATE

0 to 1685 K crystal
1685 to 3504.616 K liquid
above 3504.616 K ideal monatomic gas

Refer to the individual tables for details.

T/K	C _p ^o	Enthalpy Reference Temperature = T _r = 298.15 K		Standard State Pressure = p ^o = 0.1 MPa		log K _r
		S ^o - [G ^o - H ^o (T _r)]/T	H ^o - H ^o (T _r)	Δ _f H ^o	Δ _f G ^o	
0	0	INFINITE	0	0	0	0
100	7.268	3.833	-2.952	0	0	0
200	15.636	11.665	-1.773	0	0	0
298.15	20.000	18.820	0	0	0	0
300	20.050	18.943	0.037	0	0	0
400	22.142	25.032	2.159	0	0	0
500	23.330	30.110	4.456	0	0	0
600	24.154	34.440	6.812	0	0	0
700	24.803	38.212	9.260	0	0	0
800	25.359	41.562	11.769	0	0	0
900	25.874	44.579	14.331	0	0	0
1000	26.338	47.329	16.942	0	0	0
1100	26.778	49.860	19.598	0	0	0
1200	27.196	52.208	22.297	0	0	0
1300	27.614	54.401	25.037	0	0	0
1400	28.033	56.463	27.820	0	0	0
1500	28.451	58.411	30.644	0	0	0
1600	28.870	60.261	33.510	0	0	0
1685.000	29.225	61.765	35.979	CRYSTAL <- -> LIQUID	0	0
1685.000	27.196	91.562	40.412	TRANSITION	0	0
1700	27.196	91.803	40.864	0	0	0
1800	27.196	93.357	43.738	0	0	0
1900	27.196	94.827	46.388	0	0	0
2000	27.196	96.222	48.846	0	0	0
2100	27.196	97.549	51.133	0	0	0
2200	27.196	98.815	53.272	0	0	0
2300	27.196	100.023	55.279	0	0	0
2400	27.196	101.181	57.167	0	0	0
2500	27.196	102.291	58.950	0	0	0
2600	27.196	103.358	60.638	0	0	0
2700	27.196	104.384	62.239	0	0	0
2800	27.196	105.373	63.762	0	0	0
2900	27.196	106.327	65.214	0	0	0
3000	27.196	107.249	66.600	0	0	0
3100	27.196	108.141	67.925	0	0	0
3200	27.196	109.005	69.196	0	0	0
3300	27.196	109.842	70.415	0	0	0
3400	27.196	110.653	71.586	0	0	0
3500	27.196	111.442	72.714	0	0	0
3504.616	27.196	111.478	72.765	LIQUID <- -> IDEAL GAS	0	0
3504.616	23.023	221.204	72.765	FUGACITY = 1 bar	0	0
3600	23.046	221.822	76.706	0	0	0
3700	23.066	222.454	80.637	0	0	0
3800	23.081	223.070	84.377	0	0	0
3900	23.093	223.669	87.941	0	0	0
4000	23.102	224.254	91.341	0	0	0
4100	23.108	224.825	94.590	0	0	0
4200	23.111	225.381	97.698	0	0	0
4300	23.113	225.925	100.673	0	0	0
4400	23.112	226.457	103.526	0	0	0
4500	23.111	226.976	106.264	0	0	0
4600	23.108	227.484	108.893	0	0	0
4700	23.104	227.981	111.422	0	0	0
4800	23.100	228.467	113.855	0	0	0
4900	23.096	228.943	116.199	0	0	0
5000	23.092	229.410	118.459	0	0	0
5100	23.089	229.867	120.639	0	0	0
5200	23.087	230.316	122.744	0	0	0
5300	23.086	230.755	124.777	0	0	0
5400	23.086	231.187	126.744	0	0	0
5500	23.087	231.610	128.647	0	0	0
5600	23.091	232.026	130.489	0	0	0
5700	23.098	232.435	132.274	0	0	0
5800	23.108	232.837	134.005	0	0	0
5900	23.121	233.232	135.683	0	0	0
6000	23.135	233.621	137.312	0	0	0

PREVIOUS: March 1967 (1 atm)

CURRENT: March 1967 (1 bar)

Silicon (Si)

Si_l(ref)

CRYSTAL

Silicon (Si)

$$S^{\circ}(298.15 \text{ K}) = 18.820 \pm 0.04 \text{ J}\cdot\text{K}^{-1}\cdot\text{mol}^{-1}$$

$$T_{\text{fus}} = 1685 \pm 3 \text{ K}$$

Enthalpy of Formation

Zero by definition.

Heat Capacity and Entropy

Low temperature heat capacities are based on the precise data of Flubacher *et al.* (8–300 K).¹ The entropy is obtained from the heat capacity using $S^{\circ}(8 \text{ K}) = 0.0003 \text{ cal}\cdot\text{K}^{-1}\cdot\text{mol}^{-1}$. The selected values are consistent with recent data of Keesom and Seidel (1.2–4.2 K),² and Kalishевич *et al.* (60–300 K).³ Earlier data have been reviewed by Hultgren *et al.*⁴

High temperature studies are summarized below along with the pertinent low temperature studies. The selected heat capacities above 300 K are obtained from a Shomate plot of the adopted low temperature heat capacities and the enthalpies reported or derived from the work of Dennison,⁵ Kantor *et al.*,⁶ Oletie, Serbrennikov and Gel'd,⁷ and Magnus.⁸ Discrepancies are apparent in the enthalpy data, particularly in the range of 370–1100 K where only the recent study of Dennison⁵ made use of a high purity sample. Enthalpies from Dennison⁵ join most smoothly with the low temperature heat capacity but deviate increasingly at higher temperatures, being 1–2% lower than the other measurements above 1000 K. The selected functions agree with Dennison⁵ below 600 K, with Magnus⁸ from 600 to 1200 K, and with Kantor *et al.*⁶ above 1200 K. The resulting heat capacities are slightly different from those selected by Hultgren, *et al.*,⁴ the latter are 0.07 cal $\cdot\text{K}^{-1}\cdot\text{mol}^{-1}$ higher at 800 K and 0.21 cal $\cdot\text{K}^{-1}\cdot\text{mol}^{-1}$ lower at the melting point.

Source	Method	Quantity Reported	T/K	Sample
1	Calorimetry	C_p°	7.7–300	Single crystal, 3mm pieces, Resistance (300 K) = 100 ohm cm, Carrier Concentration $\leq 10^{19} \text{ cm}^{-3}$
2	Calorimetry	Specific Heat	1.2–4.2	
3	Calorimetry	C_p°	60–300	
4	Temperature Modulation	C_p°	300–900	99.9999% Resistance (300 K) = 0.027 ohm cm, Carrier Concentration = 10^{19} cm^{-3}
5	Drop Calorimetry	Specific Heat	273–1373	Resistance (300 K) = 107 ohm cm
6	Drop Calorimetry	Enthalpy Equation	1148–1685	Carrier Concentration = 10 ¹⁹ cm ⁻³
7	Drop Calorimetry	Specific Enthalpy	1467–1685	"Highly purified"
8	Drop Calorimetry	Specific Enthalpy	302 – 1556	99.99%
9	Drop Calorimetry	Specific Enthalpy	372 – 1175	99.2%

Fusion Data

Refer to the liquid table for details.

Sublimation Data

Refer to the ideal gas table for details.

References

- ¹P. Flubacher, A. J. Leadbetter and J. A. Morrison, *Phil. Mag.* **4**, 275 (1959).
- ²P. H. Keesom and G. Seidel, *Phys. Rev.* **113**, 33 (1959).
- ³G. I. Kalishевич, P. V. Gel'd, and R. P. Krentsis, *Russ. J. Phys. Chem.* **39**, 1602 (1965).
- ⁴D. Gerlich, B. Abeles and R. E. Miller, *J. Appl. Phys.* **36**, 76 (1965).
- ⁵D. H. Dennison, quoted by H. R. Shanks *et al.*, *Phys. Rev.* **130**, 1743 (1963).
- ⁶P. B. Kantor, A. M. Kisil and E. M. Fomicheva, *Ukrain. Fiz. Zhur.* **5**, 358 (1960).
- ⁷M. Oletie, *Phys. Chem. Steelmaking, Proc. Dedham, Mass.* **1956**, 18–26 (Pub. 1958).
- ⁸N. N. Serbrennikov and P. V. Gel'd, *Dokl. Akad. Nauk SSSR* **87**, 1021 (1952).
- ⁹A. Magnus, *Ann. Physik* **70**, 303 (1923).
- ¹⁰R. Hultgren, R. L. Orr, and K. K. Kelley, "Supplement to Selected Values of Thermodynamic Properties of Metals and Alloys," University of California, Berkeley, (1965).

Silicon (Si)

Si_l(cr)

T/K	Enthalpy Reference Temperature = T _r = 298.15 K		Standard State Pressure = P ^o = 0.1 MPa		log K _r
	C _p ^o	S ^o - (G ^o - HF(T _r))/T	H ^o - H ^o (T _r)	ΔG ^o	
0	0	0	-3.218	0	0
100	7.268	33.551	-2.952	0	0
200	15.636	11.665	-1.773	0	0
250	18.221	15.446	-0.923	0	0
298.15	20.000	18.820	0	0	0
300	20.050	18.820	0.037	0	0
350	21.276	22.132	1.072	0	0
400	22.142	25.032	2.159	0	0
450	22.803	27.680	3.283	0	0
500	23.330	30.110	4.436	0	0
600	24.154	34.440	6.812	0	0
700	24.803	38.212	9.260	0	0
800	25.359	41.562	11.769	0	0
900	25.874	44.579	14.331	0	0
1000	26.338	47.329	16.942	0	0
1100	26.778	49.860	19.598	0	0
1200	27.196	52.208	22.297	0	0
1300	27.614	54.401	25.037	0	0
1400	28.033	56.463	27.820	0	0
1500	28.451	58.411	30.644	0	0
1600	28.870	60.261	33.510	0	0
1685.000	29.225	61.765	35.979	0	0
1700	29.288	62.024	36.418	-50.177	-0.014
1800	29.706	63.710	39.268	-49.947	-0.099
1900	30.125	65.327	42.359	-49.675	-0.175
2000	30.543	66.883	44.187	-49.361	-0.243
2100	30.962	68.383	45.303	-49.006	-0.305
2200	31.380	69.833	46.386	-48.608	-0.360
2300	31.798	71.237	47.436	-48.169	-0.410
2400	32.217	72.600	48.456	-47.688	-0.455
2500	32.635	73.923	49.448	-47.165	-0.496

PREVIOUS: December 1962

CURRENT: December 1966

Silicon (Si)

Si_l(cr)

Si(l) = 28.0855 Silicon (Si)

LIQUID

Silicon (Si)

$S^{\circ}(298.15\text{ K}) = [44.460] \text{ J}\cdot\text{K}^{-1}\cdot\text{mol}^{-1}$
 $T_{\text{fus}} = 1685 \pm 3 \text{ K}$
 $\Delta H^{\circ}(298.15\text{ K}) = [48.470] \text{ kJ}\cdot\text{mol}^{-1}$
 $\Delta_{\text{vap}}H^{\circ} = 50.2 \pm 0.4 \text{ kJ}\cdot\text{mol}^{-1}$

Enthalpy of Formation

The enthalpy of formation, $\Delta H^{\circ}(\text{Si}, l, 298.15\text{ K})$ is calculated from that of the crystal by adding $\Delta_{\text{fus}}H^{\circ}$ and the difference in enthalpy, $H^{\circ}(1685\text{ K}) - H^{\circ}(298.15\text{ K})$, between the crystal and liquid.

Heat Capacity and Entropy

Enthalpy data for high purity samples in quartz or vitreous silica capsules have been reported for the range 1698–1915 K by Kantor *et al.*¹ and for the range 1686–1825 K by Olette.² Due to the limited temperature range and the experimental uncertainty, the data do not appear to justify more than a constant heat capacity. A value of $6.5 \text{ cal}\cdot\text{K}^{-1}\cdot\text{mol}^{-1}$ is selected, intermediate between the values of 6.75 and 6.15 obtained from separate experiments.

The entropy is calculated in a manner analogous to that used for the enthalpy of formation.

Fusion Data

Modern determinations of the melting point range from 1683 ± 1 to $1690 \pm 4 \text{ K}$, the former from the specific volume study of Lucas and Urbain³ and the later from the enthalpy study of Kantor *et al.*¹ The selected value, $T_{\text{fus}} = 1685 \text{ K}$, is taken from Hultgren *et al.*,⁴ who have reviewed the melting data.

The enthalpy of melting is calculated from the selected enthalpy of the crystal and the liquid enthalpy measurements of Kantor *et al.*¹ and Olette,² who reported comparable values of $\Delta_{\text{fus}}H^{\circ} = 11.95 \pm 0.18$ and $12.095 \pm 0.1 \text{ kcal}\cdot\text{mol}^{-1}$, respectively.

Vaporization Data

T_{vap} is calculated as the temperature for which $\Delta_r G^{\circ} = 0$ for $\text{Si}(l) = \text{Si}(g)$. $\Delta_{\text{vap}}H^{\circ}$ is calculated as the difference between $\Delta H^{\circ}(g)$ and $\Delta H^{\circ}(l)$ at T_{vap} . The normal boiling for the equilibrium vapor is calculated as the temperature at which Si_2 , Si_3 , and Si_4 attain a total pressure of 1 atm; the vapor containing 92.1%, 7.0% and 0.9% (mole) of monomer, dimer, and trimer, respectively. Tetramer and high polymers, which are ignored in this calculation, are probably negligible at this temperature ($\sim 3490 \text{ K}$).

References

1. P. B. Kantor, A. M. Kisil, and E. M. Fomichev, *Ukrain. Fiz. Zhur.* **5**, 358 (1960).
2. M. Olette, *Phys. Chem. Steelmaking, Proc. Dedham, Mass. 1956*, 18–26 (Pub. 1958).
3. L. D. Lucas and G. Urbain, *Compt. Rend.* **255**, 2414 (1962).
4. R. Hultgren, R. L. Orr and K. K. Kelley, "Supplement to Selected Values of Thermodynamic Properties of Metals and Alloys," Univ. of California, Berkeley, (1965).

T/K	C _p	Enthalpy Reference Temperature = T _r = 298.15 K		Standard State Pressure = P ^o = 0.1 MPa		log K _r
		S ^o - [G ^o - H ^o (T)]/T	H ^o - H ^o (T)	ΔH ^o	ΔG ^o	
0						
100						
200						
250						
298.15	27.196	44.460	44.460	48.470	40.826	-7.152
300	27.196	44.628	44.461	48.483	40.778	-7.100
350	27.196	48.821	44.792	48.808	39.467	-3.890
400	27.196	52.432	45.227	49.082	38.114	-4.977
450	27.196	55.655	46.478	49.317	36.728	-4.263
500	27.196	58.521	47.542	49.523	35.318	-3.690
600	27.196	63.479	49.797	49.867	32.824	-2.824
700	27.196	67.671	52.059	50.139	29.517	-2.203
800	27.196	71.303	54.243	50.349	26.556	-1.734
900	27.196	74.506	56.320	50.507	23.572	-1.368
1000	27.196	77.372	58.284	50.616	20.573	-1.075
1100	27.196	79.964	60.139	50.679	17.565	-0.834
1200	27.196	82.330	61.891	50.700	14.554	-0.634
1300	27.196	84.507	63.548	50.679	11.542	-0.464
1400	27.196	86.522	65.118	50.616	8.534	-0.318
1500	27.196	88.399	66.608	50.512	5.531	-0.193
1600	27.196	90.154	68.026	50.365	2.537	-0.083
1685.000	27.196	91.562	69.178	50.175	0.000	---
1700	27.196	91.803	69.376	50.150	0.000	---
1800	27.196	93.571	70.866	50.000	0.000	---
1900	27.196	94.899	71.899	49.844	0.000	---
2000	27.196	96.222	73.081	49.688	0.000	---
2100	27.196	97.549	74.215	49.532	0.000	---
2200	27.196	98.814	75.304	49.376	0.000	---
2300	27.196	100.023	76.353	49.220	0.000	---
2400	27.196	101.181	77.363	49.064	0.000	---
2500	27.196	102.291	78.338	48.908	0.000	---
2600	27.196	103.358	79.280	48.752	0.000	---
2700	27.196	104.384	80.191	48.596	0.000	---
2800	27.196	105.373	81.073	48.440	0.000	---
2900	27.196	106.327	81.928	48.284	0.000	---
3000	27.196	107.249	82.756	48.128	0.000	---
3100	27.196	108.141	83.561	47.972	0.000	---
3200	27.196	109.005	84.343	47.816	0.000	---
3300	27.196	109.842	85.103	47.660	0.000	---
3400	27.196	110.653	85.842	47.504	0.000	---
3500	27.196	111.442	86.562	47.348	0.000	---
3504.616	27.196	111.478	86.595	47.348	0.000	---
3600	27.196	112.208	87.264	47.192	0.000	---
3700	27.196	112.953	87.949	47.036	0.000	---
3800	27.196	113.678	88.616	46.880	0.000	---
3900	27.196	114.385	89.268	46.724	0.000	---
4000	27.196	115.073	89.904	46.568	0.000	---
4100	27.196	115.745	90.526	46.412	0.000	---
4200	27.196	116.400	91.135	46.256	0.000	---
4300	27.196	117.040	91.730	46.100	0.000	---
4400	27.196	117.665	92.312	45.944	0.000	---
4500	27.196	118.277	92.882	45.788	0.000	---

PREVIOUS: December 1966

CURRENT: March 1967

Silicon (Si)

Si(l)

Silicon (Si)

CRYSTAL-LIQUID

A_r = 28.0855 Silicon (Si)

Si₁(cr,l)

0 to 1685 K crystal
above 1685 K liquid

Refer to the individual tables for details.

T/K	C _p ^o	Enthalpy Reference Temperature = T _r = 298.15 K		Standard State Pressure = p ^o = 0.1 MPa		log K _r
		$\int_0^T C_p^o dT$ / J·K ⁻¹ ·mol ⁻¹	$S^o - (G^o - H^o(T_r))/T_r$	$H^o - H^o(T_r)$ / kJ·mol ⁻¹	$\Delta_f G^o$	
0	0	0	INFINITE	0	0	0
100	72.68	3.833	0	-3.218	0	0
200	15.656	11.665	33.351	-2.952	0	0
250	18.221	15.446	20.531	-1.773	0	0
298.15	20.000	18.820	19.138	-0.923	0	0
300	20.050	18.943	18.820	0	0	0
350	21.276	22.132	19.069	0.037	0	0
400	22.142	25.032	19.636	1.072	0	0
450	22.803	27.680	20.383	2.159	0	0
500	23.330	30.110	21.237	3.283	0	0
600	24.154	34.440	23.086	4.436	0	0
700	24.803	38.212	24.983	6.812	0	0
800	25.359	41.562	26.850	9.260	0	0
900	25.874	44.579	28.655	11.769	0	0
1000	26.338	47.329	30.387	14.331	0	0
1100	26.778	49.860	32.044	16.942	0	0
1200	27.196	52.208	33.627	19.598	0	0
1300	27.614	54.401	35.142	22.297	0	0
1400	28.033	56.463	36.592	25.037	0	0
1500	28.451	58.411	37.982	27.820	0	0
1600	28.870	60.261	39.317	30.644	0	0
1685.000	29.225	61.765	40.412	33.510	0	0
1685.000	27.196	91.562	40.412	86.187	0	0
1700	27.196	91.803	40.864	86.595	0	0
1800	27.196	93.357	43.738	89.315	0	0
1900	27.196	94.827	46.388	92.034	0	0
2000	27.196	96.222	48.846	94.754	0	0
2100	27.196	97.549	51.133	97.473	0	0
2200	27.196	98.815	53.272	100.193	0	0
2300	27.196	100.023	55.279	102.913	0	0
2400	27.196	101.181	57.167	105.632	0	0
2500	27.196	102.291	58.950	108.352	0	0
2600	27.196	103.358	60.638	111.071	0	0
2700	27.196	104.384	62.239	113.791	0	0
2800	27.196	105.373	63.762	116.511	0	0
2900	27.196	106.327	65.214	119.230	0	0
3000	27.196	107.249	66.600	121.950	0	0
3100	27.196	108.141	67.925	124.669	0	0
3200	27.196	109.005	69.196	127.389	0	0
3300	27.196	109.842	70.413	130.109	0	0
3400	27.196	110.653	71.586	132.828	0	0
3500	27.196	111.442	72.714	135.548	0	0
3504.616	27.196	111.478	72.763	135.673	0	0
3600	27.196	112.208	73.800	138.267	10.461	-0.152
3700	27.196	112.953	74.848	140.987	21.417	-0.302
3800	27.196	113.678	75.861	143.707	31.361	-0.445
3900	27.196	114.385	76.840	146.426	41.295	-0.580
4000	27.196	115.073	77.787	149.146	51.218	-0.708
4100	27.196	115.745	78.704	151.865	61.131	-0.830
4200	27.196	116.400	79.594	154.585	71.034	-0.946
4300	27.196	117.040	80.458	157.305	80.927	-1.056
4400	27.196	117.665	81.296	160.024	90.871	-1.161
4500	27.196	118.277	82.111	162.744	100.866	-1.262

PREVIOUS:

CURRENT: March 1967

Silicon (Si)

Si₁(cr,l)

Silicon (Si)

IP(Si, g) = 65747.5 ± 0.6 cm⁻¹
 S°(298.15 K) = 167.980 ± 0.035 J·K⁻¹·mol⁻¹

IDEAL GAS

Ar = 28.0855 Silicon (Si)

Δ_fH°(0 K) = 446 ± 8 kJ·mol⁻¹
 Δ_fH°(298.15 K) = 450 ± 8 kJ·mol⁻¹

Electronic Levels and Quantum Weights	g
State	
³ P ₂	0.00
³ P ₁	77.115
³ P ₀	223.157
¹ D ₂	6298.850
¹ S ₀	15394.370

Enthalpy of Formation

The enthalpy of formation of silicon gas is chosen to be the value recommended by CODATA.¹ This value was calculated from the sublimation and decomposition measurements of Davis *et al.* (1848–2003 K),² Grieverson and Alcock (1940–2054 K),³ Drowart *et al.*,⁴ Gulbranson *et al.* (1373–1623 K),⁵ Batdorf and Smits (1493–1601 K),⁶ and Zenbov *et al.*⁷

Heat Capacity and Entropy

The information on electronic energy levels and quantum weights, given by Moore,^{8,9} is incomplete because many theoretically predicted levels have not been observed. Our calculations indicate that any reasonable method of filling in these missing levels (for *n* < 11) and cutting off the summation in the partition function¹⁰ has no effect on the thermodynamic functions to 6000 K. This is a result of the high energy of all levels other than those listed above; the next excited state is approximately 33376 cm⁻¹ above the ground state. Although we list only a few levels, all levels given by Moore^{8,9} and estimated levels (for *n* < 11) are considered in the calculation. The reported uncertainty is S°(298.15 K) is due to uncertainties in the relative atomic mass and the fundamental constants. Extension of these calculations above 6000 K may require consideration of the excited states (for *n* < 10) and use of different fill and cutoff procedures.¹⁰

The termal functions at 298.15 K closely agree with the recent CODATA recommendations¹ except for two minor changes. First, the entropy differs by 0.1094 J·K⁻¹·mol⁻¹ because this table uses a reference pressure of 1 bar, whereas CODATA recommendations are based on 1 atm. Second, the entropy differs by ~0.001 J·K⁻¹·mol⁻¹ due to the use of slightly different values for the fundamental constants.

References

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Si(g)

T/K	Enthalpy Reference Temperature = T _r = 298.15 K		Standard State Pressure = p° = 0.1 MPa		log K _r
	C _p ^o	S° - (G° - F°(T _r))/T	H° - F°(T _r)	Δ _f H°	
0	0	INFINITE	-7.550	445.668	INFINITE
100	28.072	149.886	-4.809	448.142	-226.271
200	23.796	170.034	-2.247	449.526	-109.718
250	22.821	164.013	-1.084	449.839	-69.228
298.15	22.251	167.980	0	450.000	-71.047
300	22.234	168.117	0.041	450.004	-70.561
350	21.861	171.515	1.143	450.071	-59.366
400	21.613	174.417	2.229	450.071	-50.970
450	21.440	176.952	3.305	450.023	-44.440
500	21.316	179.204	4.374	449.938	-39.217
600	21.153	183.075	6.497	449.684	-31.385
700	21.037	188.328	8.607	449.347	-25.794
800	20.951	193.135	10.710	448.940	-21.504
900	20.897	197.507	12.808	448.476	-18.349
1000	20.868	199.816	14.905	447.962	-15.747
1100	20.859	199.815	17.002	447.404	-13.622
1200	21.033	197.643	19.103	446.806	-11.852
1300	21.099	193.329	21.210	446.172	-10.557
1400	21.183	200.896	23.323	445.504	-9.078
1500	21.282	207.360	25.447	444.803	-7.970
1600	21.394	203.737	27.580	444.070	-7.003
1700	21.513	200.038	29.726	443.311	-6.165
1800	21.638	206.271	31.883	442.529	-5.494
1900	21.764	207.444	34.053	441.727	-4.895
2000	21.889	208.564	36.236	440.902	-4.356
2100	22.011	209.635	38.431	440.058	-3.870
2200	22.129	210.662	40.638	439.198	-3.426
2300	22.241	211.648	42.857	438.328	-3.012
2400	22.346	212.591	45.086	437.454	-2.625
2500	22.444	213.511	47.326	436.578	-2.268
2600	22.535	214.393	49.575	435.703	-1.941
2700	22.617	215.245	51.832	434.828	-1.644
2800	22.692	216.069	54.098	433.953	-1.377
2900	22.759	216.866	56.370	433.078	-1.139
3000	22.819	217.639	58.649	432.203	-0.927
3100	22.872	218.388	60.934	431.328	-0.750
3200	22.918	219.115	63.223	430.453	-0.607
3300	22.958	219.821	65.517	429.578	-0.556
3400	22.993	220.507	67.815	428.703	-0.516
3500	23.022	221.174	70.116	427.828	-0.488
3504.616	23.022	221.204	70.222	427.828	0.507
3600	23.046	221.822	72.419	426.953	0
3700	23.066	222.434	74.725	426.078	0
3800	23.081	223.070	77.032	425.203	0
3900	23.093	223.699	79.341	424.328	0
4000	23.102	224.254	81.651	423.453	0
4100	23.108	224.825	83.961	422.578	0
4200	23.111	225.381	86.272	421.703	0
4300	23.113	225.925	88.583	420.828	0
4400	23.112	226.457	90.895	420.000	0
4500	23.111	226.976	93.206	419.175	0
4600	23.108	227.484	95.517	418.350	0
4700	23.104	227.981	97.827	417.525	0
4800	23.100	228.467	100.138	416.700	0
4900	23.096	228.943	102.447	415.875	0
5000	23.092	229.410	104.757	415.050	0
5100	23.089	229.867	107.066	414.225	0
5200	23.087	230.316	109.375	413.400	0
5300	23.086	230.735	111.683	412.575	0
5400	23.086	231.187	113.992	411.750	0
5500	23.087	231.610	116.300	410.925	0
5600	23.091	232.026	118.609	410.100	0
5700	23.098	232.435	120.918	409.275	0
5800	23.108	232.837	123.228	408.450	0
5900	23.121	233.232	125.539	407.625	0
6000	23.135	233.621	127.851	406.800	0

PREVIOUS: March 1967 (1 atm) CURRENT: March 1983 (1 bar)

Silicon (Si)

Si(g)

Silicon, Ion (Si⁺)

IP(Si⁺, g) = 131838.4 ± 0.1 cm⁻¹
 S^o(298.15 K) = 163.426 ± 0.02 J·K⁻¹·mol⁻¹

IDEAL GAS

Electronic Levels and Quantum Weights	g _i
State	g _i
² P _{1/2}	0.0
² P _{3/2}	2
⁴ P _{1/2}	4
⁴ P _{3/2}	4
⁴ P _{5/2}	6
⁴ F _{3/2}	4

M_r = 28.08495

Δ_rH^o(0 K) = 1232.2 ± 4 kJ·mol⁻¹
 Δ_rH^o(298.15 K) = [1242.505] kJ·mol⁻¹

Silicon, Ion (Si⁺)

Enthalpy Reference Temperature = T_r = 298.15 K

S^o - (S^o - H^o(T_r))/T

J·K⁻¹·mol⁻¹

C_p^o

T/K

H^o - H^o(T_r)

kJ·mol⁻¹

Δ_rH^o

A·G^o

log K_r

Standard State Pressure = P^o = 0.1 MPa

Si(g)

T/K	C _p ^o	S ^o - (S ^o - H ^o (T _r))/T	H ^o - H ^o (T _r)	Δ _r H ^o	A·G ^o	log K _r
0	0	INFINITE	-7.343	1232.183		
100	25.060	134.836	-7.343	1232.183	1193.136	-209.032
200	26.512	153.262	-5.158	1232.183	192.829	-207.690
250	25.337	159.052	-2.491	1232.183	184.446	-176.769
298.15	24.338	163.426	0	1242.505	175.897	-135.556
300	24.304	163.577	0.045	1242.551	167.213	-135.487
400	23.520	167.261	1.240	1243.750	158.414	-121.019
450	22.943	170.562	2.400	1244.864	140.292	-99.292
500	22.518	173.039	3.536	1245.915	122.342	-83.750
600	22.201	175.594	4.654	1246.918	104.747	-70.077
700	21.773	178.400	5.851	1248.818	88.159	-62.986
800	21.509	182.735	7.014	1250.611	72.570	-57.704
900	21.337	188.101	8.156	1252.323	58.054	-49.738
1000	21.219	193.342	9.283	1253.967	44.738	-40.544
1100	21.134	198.332	10.401	1255.552	32.597	-33.787
1200	21.072	193.344	11.511	1257.085	21.607	-31.037
1300	21.025	188.175	12.615	1258.570	11.479	-28.622
1400	20.989	182.857	13.716	1260.008	1.199	-26.547
1500	20.960	177.411	14.814	1261.402	-8.989	-24.888
1600	20.937	171.884	15.908	1262.751	-18.519	-23.622
1700	20.918	166.266	17.000	1264.056	-28.622	-22.704
1800	20.903	160.569	18.092	1265.322	-39.399	-22.119
1900	20.890	154.797	19.184	1266.552	-50.814	-21.811
2000	20.879	148.960	20.276	1267.751	-62.864	-21.648
2100	20.870	143.069	21.368	1268.924	-75.544	-21.688
2200	20.862	137.133	22.460	1270.074	-88.951	-21.878
2300	20.855	131.161	23.552	1271.204	-103.083	-22.204
2400	20.849	125.161	24.644	1272.312	-117.939	-22.664
2500	20.844	119.133	25.736	1273.400	-133.526	-23.264
2600	20.839	113.088	26.828	1274.470	-149.864	-24.000
2700	20.835	107.024	27.920	1275.524	-166.964	-24.878
2800	20.831	100.941	29.012	1276.564	-184.836	-25.900
2900	20.828	94.839	30.104	1277.590	-203.480	-27.072
3000	20.825	88.716	31.196	1278.604	-222.900	-28.396
3100	20.822	82.583	32.288	1279.604	-243.112	-30.872
3200	20.818	76.440	33.380	1280.592	-264.224	-33.504
3300	20.816	70.287	34.472	1281.568	-286.248	-36.296
3400	20.814	64.124	35.564	1282.532	-309.192	-39.248
3500	20.813	57.951	36.656	1283.484	-333.056	-42.368
3600	20.811	51.768	37.748	1284.424	-357.840	-45.648
3700	20.810	45.575	38.840	1285.352	-383.552	-49.088
3800	20.809	39.372	39.932	1286.268	-410.192	-52.688
3900	20.808	33.159	41.024	1287.172	-437.768	-56.448
4000	20.807	26.936	42.116	1288.064	-466.288	-60.368
4100	20.807	20.713	43.208	1288.944	-495.752	-64.448
4200	20.806	14.490	44.300	1289.812	-526.168	-68.688
4300	20.806	8.267	45.392	1290.668	-557.536	-73.096
4400	20.806	2.044	46.484	1291.512	-589.864	-77.672
4500	20.806	-4.179	47.576	1292.344	-623.160	-82.416
4600	20.806	-10.402	48.668	1293.164	-657.424	-87.328
4700	20.805	-16.624	49.760	1293.972	-702.656	-92.408
4800	20.805	-22.847	50.852	1294.768	-748.864	-97.648
4900	20.805	-29.070	51.944	1295.552	-806.048	-103.048
5000	20.811	-35.293	53.036	1296.324	-864.288	-108.608
5100	20.813	-41.516	54.128	1297.084	-923.584	-114.328
5200	20.816	-47.739	55.220	1297.832	-983.936	-120.208
5300	20.819	-53.962	56.312	1298.568	-1045.344	-126.248
5400	20.822	-60.185	57.404	1299.292	-1107.816	-132.448
5500	20.827	-66.408	58.496	1300.004	-1171.344	-138.808
5600	20.832	-72.631	59.588	1300.704	-1235.936	-145.328
5700	20.838	-78.854	60.680	1301.392	-1301.584	-152.008
5800	20.845	-85.077	61.772	1302.068	-1368.296	-158.848
5900	20.852	-91.300	62.864	1302.732	-1436.064	-165.848
6000	20.861	-97.523	63.956	1303.384	-1504.896	-173.008

PREVIOUS: December 1971 (1 atm)

CURRENT: March 1983 (1 bar)

Enthalpy of Formation

Δ_rH^o(Si⁺, g, 0 K) is calculated from Δ_rH^o(Si, g, 0 K) using the spectroscopic value of IP(Si) = 65747.5 ± 0.6 cm⁻¹ (786.515 ± 0.001 kJ·mol⁻¹) from Moore.^{2,6} The ionization limit is converted from cm⁻¹ to kJ·mol⁻¹ using the factor, 1 cm⁻¹ = 0.01196266 kJ·mol⁻¹, which is derived from the 1973 CODATA fundamental constants.³ Rosenstock *et al.*,⁴ and Levin and Lias⁵ have summarized additional ionization and appearance potential data.

Δ_rH^o(Si⁺, g, 298.15 K) is calculated from Δ_rH^o(Si, g, 0 K) by using IP(Si) with JANAF¹ enthalpies, H^o(0 K) - H^o(298.15 K), for Si(g), Si⁺(g), and e⁻ (ref). Δ_rH^o(Si⁺ → Si⁺ + e⁻, 298.15 K) differs from a room temperature threshold energy due to inclusion of these enthalpies and to threshold effects discussed by Rosenstock *et al.*,⁴ Δ_rH^o(298.15 K) should be changed by -6.197 kJ·mol⁻¹ if it is to be used in the ion convention that excludes the enthalpy of the electron.

Heat Capacity and Entropy

The information on electronic energy levels and quantum weights, given by Moore,^{2,6} is incomplete because many theoretically predicted levels have not been observed. Our calculations indicate that any reasonable method of filling in these missing levels and cutting off the summation in the partition function⁷ has no effect on the thermodynamic functions to 6000 K. This is a result of the high energy of all levels other than the ground state and the first four excited states; the next excited state is 55309.61 cm⁻¹ above the ground state. Since inclusion of these excited states has no effect on the thermodynamic functions (to 6000 K), we list only the ground state and the first four excited states. The reported uncertainty in S^o(298.15 K) is due to uncertainties in the relative ionic mass and the fundamental constants. Extension of these calculations above 6000 K may require consideration of the excited states and use of different fill and cutoff procedures.⁷

References

- ¹JANAF Thermochemical Tables: Si (g), 3-31-83; e⁻ (ref), 3-31-82.
- ²C. E. Moore, U. S. Nat. Bur. Stand., NSRDS-NBS-34, 8 pp. (1970).
- ³E. R. Cohen and B. N. Taylor, J. Phys. Chem. Ref. Data 2, 663 (1973).
- ⁴H. M. Rosenstock, K. Draxl *et al.*, J. Phys. Chem. Ref. Data 6, Supp. 1, 783 pp. (1977).
- ⁵R. D. Levin and S. G. Lias, U. S. Nat. Bur. Stand., NSRDS-NBS-71, 634 pp. (1982).
- ⁶C. E. Moore, U. S. Nat. Bur. Stand., NSRDS-NBS-3, Section I (1965) and Section II (1967).
- ⁷J. R. Downey, Jr., The Dow Chemical Company, AFOSR-TR-0960, Contract No. F44620-75-1-0048, (1978).

Silicon, Ion (Si⁺)

Si(g)

Silicon, Ion (Si⁺)

EA(Si, g) = 1.385 ± 0.005 eV
 S°(298.15 K) = 161.977 ± 0.001 J·K⁻¹·mol⁻¹

IDEAL GAS

Electronic Levels and Quantum Weights State	ε _n , cm ⁻¹	g _n
4s	0	4
3d	6952	10
3p	10937	6

Enthalpy of Formation

Δ_fH°(Si⁺, g, 0 K) is calculated from Δ_fH°(Si, g, 0 K)¹ using the adopted electron affinity of EA(Si) = 1.385 ± 0.005 eV (133.631 ± 0.482 kJ·mol⁻¹). This value, recommended by Hotop and Lineberger,² is based on a laser photodetachment electron spectroscopy study.³ Additional information on Si⁺(g) may be obtained in the critical discussions of Hotop and Lineberger,² Rosenstock *et al.*,⁴ and Massey.⁵ Δ_fH°(Si⁺, g, 298.15 K) is obtained from Δ_fH°(Si, g, 0 K) by using EA(Si) with JANAF¹ enthalpies, H°(0 K) - H°(298.15 K), for Si⁺(g), Si(g), and e⁻ (ref) Δ_fH°(Si⁺ → Si + e⁻, 298.15 K) differs from a room-temperature threshold energy due to inclusion of these enthalpies and to threshold effects discussed by Rosenstock *et al.*,⁴ Δ_fH°(298.15 K) should be changed by + 6.197 kJ·mol⁻¹ if it is to be used in the ion convention that excludes the enthalpy of the electron.

Heat Capacity and Entropy

Electronic energy levels are from the laser photodetachment electron spectroscopy study of Kasdan *et al.*,³ These workers found that the Si⁺(²D) and Si⁺(²P) states have binding energies of 0.523 ± 0.005 eV and 0.029 ± 0.005 eV, respectively, relative to ground state Si⁺(⁴S₀). The electronic energies of 6952 cm⁻¹ and 10937 cm⁻¹ are the difference in binding energy between ground and excited states. We neglect the spin-orbit splitting of the ²D and ²P states; its effect is negligible.

References

- JANAF Thermochemical Tables: Si(g), 3-31-83; e⁻(ref), 3-31-82.
- H. Hotop and W. C. Lineberger, *J. Phys. Chem. Ref. Data*, **14**, 731 (1985).
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- H. M. Rosenstock, K. Draxl *et al.*, *J. Phys. Chem. Ref. Data* **6**, Supp. 1, 783 pp. (1977).
- H. S. W. Massey, "Negative Ions", 3rd ed., Cambridge University Press, Cambridge, 741 pp. (1976).

M_r = 28.08605 Silicon, Ion (Si⁻)

Δ_fH°(0 K) = 312.04 ± 3 kJ·mol⁻¹
 Δ_fH°(298.15 K) = [308.819] kJ·mol⁻¹

T/K	C _p ^o	Enthalpy Reference: Temperature = T _r = 298.15 K		Standard State Pressure = p° = 0.1 MPa		log K _r
		S° - [C _p - H°(T _r)]/T	H° - H°(T _r)/T	Δ _f H°	Δ _f G°	
0	0	INFINITE	-6.197	312.037		
100	20.786	139.270	-4.119			-47.722
200	20.786	183.578	-2.040			-47.388
250	20.786	198.516	-1.001			-47.165
298.15	20.786	161.977	0	308.819		-47.165
300	20.786	162.106	0.078			-47.165
350	20.786	165.310	1.078			-47.165
400	20.786	168.085	2.117			-47.165
450	20.786	170.534	3.156			-47.165
500	20.786	172.724	4.196			-47.165
600	20.786	176.513	6.274			-47.165
700	20.787	179.718	8.353			-47.165
800	20.791	182.494	10.432			-47.165
900	20.803	184.943	12.511			-47.165
1000	20.831	187.136	14.593			-47.165
1100	20.887	189.124	16.678			-47.165
1200	20.981	190.945	18.771			-47.165
1300	21.122	192.629	20.876			-47.165
1400	21.318	194.202	22.998			-47.165
1500	21.572	195.681	25.142			-47.165
1600	21.884	197.082	27.314			-47.165
1700	22.253	198.420	29.520			-47.165
1800	22.674	199.704	31.766			-47.165
1900	23.140	200.942	34.057			-47.165
2000	23.645	202.141	36.396			-47.165
2100	24.179	203.308	38.787			-47.165
2200	24.735	204.445	41.232			-47.165
2300	25.303	205.558	43.734			-47.165
2400	25.876	206.646	46.293			-47.165
2500	26.444	207.714	48.909			-47.165
2600	27.002	208.762	51.581			-47.165
2700	27.542	209.792	54.309			-47.165
2800	28.058	210.803	57.089			-47.165
2900	28.548	211.796	59.920			-47.165
3000	29.003	212.772	62.797			-47.165
3100	29.428	213.750	65.719			-47.165
3200	29.815	214.670	68.682			-47.165
3300	30.164	215.593	71.681			-47.165
3400	30.475	216.498	74.714			-47.165
3500	30.748	217.386	77.775			-47.165
3600	30.982	218.255	80.862			-47.165
3700	31.180	219.107	83.970			-47.165
3800	31.343	219.941	87.097			-47.165
3900	31.472	220.757	90.238			-47.165
4000	31.568	221.555	93.390			-47.165
4100	31.635	222.335	96.550			-47.165
4200	31.674	223.098	99.716			-47.165
4300	31.687	223.843	102.884			-47.165
4400	31.676	224.572	106.053			-47.165
4500	31.643	225.283	109.219			-47.165
4600	31.591	225.978	112.381			-47.165
4700	31.521	226.657	115.536			-47.165
4800	31.433	227.320	118.684			-47.165
4900	31.336	227.967	121.823			-47.165
5000	31.224	228.599	124.951			-47.165
5100	31.101	229.216	128.067			-47.165
5200	30.969	229.819	131.171			-47.165
5300	30.829	230.407	134.261			-47.165
5400	30.683	230.982	137.337			-47.165
5500	30.531	231.544	140.397			-47.165
5600	30.374	232.092	143.443			-47.165
5700	30.214	232.629	146.472			-47.165
5800	30.051	233.153	149.485			-47.165
5900	29.886	233.663	152.482			-47.165
6000	29.720	234.166	155.463			-47.165

PREVIOUS:

CURRENT: March 1983 (1 bar)

Silicon, Ion (Si⁺)

Si⁺(g)

Silicon (Si₂)

IDEAL GAS

M_r = 56.1710 Silicon (Si₂)

S°(298.15 K) = 229.79 J·K⁻¹·mol⁻¹ ΔH°(0 K) = 587.1 ± 13 kJ·mol⁻¹
 ΔH°(298.15 K) = 589.9 ± 13 kJ·mol⁻¹

State	ε _i , cm ⁻¹	g _i	Electronic Levels and Quantum Weights	ε _i , cm ⁻¹	g _i
Σ _g ⁺	0	3	[10000]	[30000]	6
Π _g	[2000]	6	[13000]	30769	3
[Σ _g ⁺]	[6000]	[1]	[20000]	[40000]	[2]
[Π _g]	[8000]	[2]	24583	[45000]	[1]
				46762	3

ω_{1,2} = 510.98 cm⁻¹
 B_e = 2.2390 cm⁻¹
 ω_{3,4} = 2.02 cm⁻¹
 α_{3,4} = 0.0013 cm⁻¹
 σ = 2
 r_e = 2.246 Å

Enthalpy of Formation

The selected value is based on the spectroscopic and equilibrium data summarized below. Verma and Warsaw¹ concluded from analysis of the absorption spectra that D₀⁰ = 70 ± 4 kcal·mol⁻¹. Predissociation of the H state suggested the upper limit D₀⁰ ≤ 74.0, while linear Birgen-Spencer extrapolations of the H and K states gave 78.4 and 68.9 kcal·mol⁻¹ for the ground state. By assuming that the true extrapolation would not reduce the linear extrapolation for the H state by more than half, i.e. from 26 to 13 kcal·mol⁻¹, the authors arrived at the lower limit of D₀⁰ ≥ 65.5 for the ground state.

Drowart and co-workers have used the Knudsen effusion-mass spectrometric technique to determine the vapor equilibria over the systems SiC-graphitic, SiC-silicon² and boron-carbon-silicon.³ Third law analysis of the partial pressures of Si₂ and Si over the three systems yields D₀⁰ values of 73.3, 74.3 and 70.4 kcal·mol⁻¹, which are in good agreement with the spectroscopic values. The selected value, ΔH°(298.15 K) = 141 ± 3 kcal·mol⁻¹, corresponds to D₀⁰ = 73.0 kcal·mol⁻¹.

Source	Method	T/K	Data Points	ΔH°(298.15 K), kcal·mol ⁻¹	Drift	ΔH°(298.15 K), kcal·mol ⁻¹
1	Prediss. of H state			≤ 73.4		≥ 140.0
	LEX of K state			70.3		145.1
	Extrap. of H state			≥ 66.9		≤ 148.5
2	Mass spec.	2149-2316	7	95.3 ± 7.1	74.68	
3	Mass spec.	1703-2160	9	81.0 ± 1.1	75.71	
4	Mass spec.	2166-2344	4	68.0 ± 1.6	71.76	
	*For the reaction Si ₂ (g) = 2 Si(g)					

Heat Capacity and Entropy

Vibrational and rotational constants are those obtained by Verma and Warsaw¹ through combination of their data for the H-X system with those of Douglas.⁵ Observation of the same H-X system in matrix isolation by Wellner and McLeod⁶ confirms that the lower state is the ground state. Comparison with the isoelectronic molecules C₂, BN, BeO and MgO^{7,10} suggest that there are several possible low-lying excited states in Si₂. Tentative estimates for these levels are given above, based on this comparison and on the observed states.¹⁵ These estimates are relatively uncertain and probably yield an upper limit for the entropy at temperatures where Si₂ is significant. A probable lower limit may be obtained by increasing the two Π states by 8000 cm⁻¹ and omitting the other estimated levels. This would reduce the entropy by 1.7 cal·K⁻¹·mol⁻¹ at 2000 K, corresponding to a change of 3.4 kcal·mol⁻¹ in ΔH° values based on equilibrium data.

References

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T/K	Enthalpy Reference Temperature = T _r = 298.15 K		Standard State Pressure = P° = 0.1 MPa		log K _r
	C _p	S°	H° - H°(T _r)/T	ΔH°	
0	29.412	195.317	INFINITE	587.118	INFINITE
100	32.184	216.488	258.806	570.734	-298.121
200	33.463	223.812	232.879	551.581	-144.058
250	34.452	229.793	230.355	541.924	-113.229
300	34.487	230.007	229.793	532.653	-93.319
350	35.374	235.390	229.794	522.298	-92.681
400	36.277	240.170	231.168	513.185	-78.011
450	37.096	244.487	231.412	503.705	-67.015
500	37.986	248.441	233.820	494.272	-51.636
600	39.743	255.524	236.860	475.531	-41.399
700	41.286	261.770	239.981	456.675	-34.097
800	42.472	267.365	243.061	438.455	-28.628
900	43.274	272.417	246.046	423.081	-24.381
1000	43.738	277.003	248.916	408.146	-20.988
1100	43.941	281.183	251.663	383.611	-18.216
1200	43.963	285.008	254.284	363.869	-15.910
1300	43.869	288.524	256.785	347.903	-13.962
1400	43.769	291.769	259.169	329.945	-12.298
1500	43.520	294.779	261.444	311.724	-10.855
1600	43.324	297.581	263.616	293.974	-9.597
1700	43.135	300.202	265.692	277.207	-8.518
1800	42.962	302.662	267.678	262.579	-7.707
1900	42.810	304.981	269.581	250.016	-6.983
2000	42.679	307.174	271.406	241.971	-6.334
2100	42.563	309.253	273.160	231.069	-5.748
2200	42.479	311.231	274.846	219.682	-5.216
2300	42.407	313.118	276.469	208.348	-4.732
2400	42.352	314.922	278.034	197.067	-4.289
2500	42.311	316.650	279.544	186.204	-3.883
2600	42.282	318.308	281.003	176.653	-3.509
2700	42.264	319.904	282.415	168.317	-3.163
2800	42.255	321.441	283.781	161.016	-2.844
2900	42.254	322.923	285.106	154.737	-2.546
3000	42.259	324.356	286.390	149.477	-2.270
3100	42.271	325.742	287.637	145.242	-2.012
3200	42.287	327.084	288.849	142.024	-1.771
3300	42.307	328.386	290.028	138.813	-1.545
3400	42.331	329.649	291.174	135.608	-1.333
3500	42.358	330.876	292.291	132.419	-1.133
3600	42.388	332.070	293.380	129.285	-0.949
3700	42.420	333.232	294.441	126.212	-0.773
3800	42.455	334.364	295.477	123.206	-0.606
3900	42.492	335.467	296.488	120.266	-0.450
4000	42.531	336.543	297.476	117.390	-0.302
4100	42.571	337.594	298.442	114.571	-0.161
4200	42.614	338.620	299.386	111.811	-0.026
4300	42.658	339.623	300.311	109.111	0.103
4400	42.704	340.605	301.215	106.473	0.235
4500	42.751	341.565	302.101	103.896	0.369
4600	42.800	342.505	302.969	101.380	0.505
4700	42.850	343.426	303.820	98.923	0.643
4800	42.902	344.329	304.655	96.523	0.782
4900	42.955	345.214	305.474	94.177	0.922
5000	43.010	346.082	306.277	91.881	1.063
5100	43.066	346.934	307.066	89.633	1.205
5200	43.123	347.771	307.841	87.433	1.348
5300	43.181	348.593	308.602	85.279	1.492
5400	43.241	349.401	309.350	83.169	1.637
5500	43.302	350.195	310.089	81.101	1.782
5600	43.364	350.976	310.809	79.073	1.928
5700	43.427	351.744	311.520	77.083	2.074
5800	43.492	352.500	312.220	75.131	2.220
5900	43.557	353.244	312.909	73.216	2.366
6000	43.623	353.976	313.586	71.332	2.512

PREVIOUS: March 1967 (1 atm)

CURRENT: March 1967 (1 bar)

Silicon (Si₂)

Si₂(g)

Silicon (Si₃)

IDEAL GAS

Si₃(g)

$S^\circ(298.15\text{ K}) = 267.90\text{ J}\cdot\text{K}^{-1}\cdot\text{mol}^{-1}$
 $\Delta H_f^\circ(0\text{ K}) = 632.7 \pm 42\text{ kJ}\cdot\text{mol}^{-1}$
 $\Delta H_f^\circ(298.15\text{ K}) = 636.0 \pm 42\text{ kJ}\cdot\text{mol}^{-1}$

Electronic State	Electronic Levels and Quantum Weights $\epsilon_i, \text{cm}^{-1}$	g_i
$^3\Sigma_u^-$	0	3
$^1\Pi_u$	[10000]	[6]
$^1\Pi_g$	[18000]	[2]
$^3\Sigma_g^+$	21460	3

Vibrational Frequencies and Degeneracies ν, cm^{-1}
[360](1)
[200](2)
[630](1)

$\sigma = [2]$

Point Group: [D_{3h}]
 Bond Distance: [2.25] Å
 Bond Angle: [190]°
 Rotational Constant: $B_0 = [0.059282]\text{ cm}^{-1}$

Enthalpy of Formation

The selected value is an average based on the equilibrium data summarized below. Drowart *et al.* have used the Knudsen effusion-mass spectrometric technique to determine the vapor species over the systems SiC-graphite¹ and SiC-silicon.² Third law analysis of the partial pressures of Si₃ and Si₂ yields the values 154.0 and 149.9 kcal·mol⁻¹. Both drifts suggest that the entropy may be lower than the tabulated values. It is unlikely that the entropy is in error by more than 5 cal·K⁻¹·mol⁻¹ so that most of the drift is inherent in the data. The adopted value of $\Delta_f H^\circ(298.15\text{ K}) = 152 \pm 10\text{ kcal}\cdot\text{mol}^{-1}$ includes allowance for an error of up to 5 cal·K⁻¹·mol⁻¹.

Source	Method	T/K	Points	2nd law $\Delta_f H^\circ(298.15\text{ K}), \text{kcal}\cdot\text{mol}^{-1}$	3rd law $\Delta_f H^\circ(298.15\text{ K}), \text{kcal}\cdot\text{mol}^{-1}$	Drift
1	Mass Spec.	2230-2316	2	209	169.1	-18
2	Mass Spec.	1703-1890	4	204 ± 3	173.2	-17 ± 2
*For reaction Si ₃ (g) = 3 Si(g)						

Heat Capacity and Entropy

Welmer and McLeod³ observed an absorption band near 4660 Å in matrix isolation studies. Their tentative assignment of this band as the $^3\Sigma_u^- \leftarrow ^3\Sigma_g^+$ transition of Si₃ is adopted here. A $^1\Pi_u$ state is assumed at 18000 cm⁻¹, which is 7000 and 2000 cm⁻¹ below the analogous levels⁴ for C₃ and C₂Si. Also a $^1\Pi_g$ level is assumed at 10000 cm⁻¹, presumably arising from the same molecular orbital configuration as the $^1\Pi_u$ state. The molecule is assumed to be linear with a bond distance equal to that in Si₂. Vibrational frequencies are estimated from a valence bond calculation using $k_1 = 2.16 \times 10^5$ and $k_2/k_1 = 0.11 \times 10^5\text{ dyn cm}^{-1}$. The stretching force constant is obtained from Si₂, while the bending force constant is based on C₂Si and the $^1\Pi_u$ excited state⁴ of C₃.

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T/K	Enthalpy Reference Temperature = T _r = 298.15 K			Standard State Pressure = p° = 0.1 MPa		
	C _p J·K ⁻¹ ·mol ⁻¹	S° - [G° - H°(T _r)]/T J·K ⁻¹ ·mol ⁻¹	H° - H°(T _r) kJ·mol ⁻¹	Δ _f H° kJ·mol ⁻¹	Δ _f G° kJ·mol ⁻¹	log K _r
0	0	0	0	0	0	INFINITE
100	39.149	216.004	-12.919	632.703	632.703	INFINITE
200	49.903	246.896	-9.698	635.125	914.674	-32.1073
250	52.965	258.381	-5.180	635.108	955.728	-151.066
298.15	55.055	267.898	-2.603	635.134	983.123	-121.837
300	55.122	268.239	0	635.968	983.123	-121.837
350	56.664	276.859	0.102	635.959	983.123	-121.837
400	57.787	284.502	2.899	635.651	983.123	-121.837
450	58.621	291.359	5.761	635.254	983.123	-121.837
500	59.255	297.570	8.673	634.792	983.123	-121.837
600	60.129	308.457	11.620	634.279	983.123	-121.837
700	60.986	317.770	17.593	633.123	983.123	-121.837
800	61.823	325.900	23.637	631.823	983.123	-121.837
900	62.641	333.108	29.724	630.384	983.123	-121.837
1000	63.448	339.579	35.844	628.818	983.123	-121.837
1100	64.244	345.450	41.986	627.128	983.123	-121.837
1200	65.029	350.820	48.146	625.319	983.123	-121.837
1300	65.804	355.769	54.318	623.395	983.123	-121.837
1400	66.569	360.359	60.501	621.357	983.123	-121.837
1500	67.325	364.639	66.695	619.203	983.123	-121.837
1600	68.072	368.649	72.898	616.934	983.123	-121.837
1700	68.810	372.423	79.111	614.549	983.123	-121.837
1800	69.539	375.988	85.336	612.054	983.123	-121.837
1900	70.260	379.369	91.574	609.464	983.123	-121.837
2000	70.974	382.585	97.827	606.782	983.123	-121.837
2100	71.682	385.653	104.097	604.011	983.123	-121.837
2200	72.384	388.588	110.385	601.158	983.123	-121.837
2300	73.081	391.403	116.695	598.226	983.123	-121.837
2400	73.773	394.109	123.028	595.218	983.123	-121.837
2500	74.461	396.714	129.385	592.135	983.123	-121.837
2600	75.145	399.228	135.761	589.078	983.123	-121.837
2700	75.825	401.658	142.178	586.046	983.123	-121.837
2800	76.501	404.011	148.617	583.038	983.123	-121.837
2900	77.173	406.291	155.085	580.062	983.123	-121.837
3000	77.841	408.502	161.582	577.122	983.123	-121.837
3100	78.505	410.653	168.109	574.216	983.123	-121.837
3200	79.165	412.744	174.666	571.344	983.123	-121.837
3300	79.821	414.780	181.252	568.506	983.123	-121.837
3400	80.473	416.764	187.868	565.702	983.123	-121.837
3500	81.121	418.698	194.513	562.932	983.123	-121.837
3600	81.765	420.586	201.186	560.206	983.123	-121.837
3700	82.405	422.429	207.886	557.524	983.123	-121.837
3800	83.041	424.229	214.613	554.886	983.123	-121.837
3900	83.673	425.990	221.365	552.292	983.123	-121.837
4000	84.301	427.711	228.142	549.742	983.123	-121.837
4100	84.925	429.396	234.942	547.236	983.123	-121.837
4200	85.545	431.045	241.764	544.774	983.123	-121.837
4300	86.161	432.667	248.607	542.356	983.123	-121.837
4400	86.773	434.242	255.451	540.000	983.123	-121.837
4500	87.381	435.792	262.305	537.706	983.123	-121.837
4600	87.985	437.312	269.252	535.482	983.123	-121.837
4700	88.585	438.803	276.267	533.328	983.123	-121.837
4800	89.181	440.265	283.298	531.244	983.123	-121.837
4900	89.773	441.699	290.343	529.230	983.123	-121.837
5000	90.361	443.107	297.400	527.286	983.123	-121.837
5100	90.945	444.490	304.469	525.412	983.123	-121.837
5200	91.525	445.847	311.549	523.608	983.123	-121.837
5300	92.101	447.180	318.637	521.874	983.123	-121.837
5400	92.673	448.489	325.734	520.210	983.123	-121.837
5500	93.241	449.776	332.839	518.616	983.123	-121.837
5600	93.805	451.041	340.000	517.092	983.123	-121.837
5700	94.365	452.284	347.222	515.638	983.123	-121.837
5800	94.921	453.506	354.500	514.254	983.123	-121.837
5900	95.473	454.708	361.834	512.940	983.123	-121.837
6000	96.021	455.890	369.216	511.696	983.123	-121.837

PREVIOUS: March 1967 (1 atm)

CURRENT: March 1967 (1 bar)

Silicon (Si₃)

Si₃(g)

Strontium (Sr)

$A_r = 87.62$ Strontium (Sr)

REFERENCE STATE

- 0 to 820 K crystal, alpha
- 820 to 1050 K crystal, beta
- 1050 to 1685.492 K liquid
- above 1685.492 K ideal monatomic gas

Refer to the individual tables for details.

T/K	C _p ^o	Enthalpy Reference Temperature = T _r = 298.15 K		Standard State Pressure = p ^o = 0.1 MPa		log K _r
		S ^o - (G ^o - HF(T _r))/T	H ^o - H ^o (T _r)	Δ _f H ^o	Δ _f G ^o	
0	0.	0.	INFINITE	0.	0.	0.
100	23.481	28.050	78.738	-5.568	0.	0.
200	25.757	45.209	58.112	-5.069	0.	0.
298.15	26.791	55.694	55.694	-2.581	0.	0.
300	26.809	55.859	55.694	0.	0.	0.
400	27.777	63.704	56.757	0.050	0.	0.
500	28.785	70.010	58.797	2.779	0.	0.
600	29.814	75.349	61.122	5.607	0.	0.
700	30.864	80.023	63.495	8.536	0.	0.
800	31.935	84.214	65.827	11.570	0.	0.
820.000	32.151	85.005	66.285	14.710	0.	0.
820.000	29.790	86.026	66.285	15.351	ALPHA <- -> BETA	TRANSITION
900	30.125	88.814	68.165	16.188	0.	0.
1000	30.543	92.010	70.393	18.584	0.	0.
1050.000	30.752	93.505	71.458	21.618	0.	0.
1050.000	39.463	100.582	71.458	23.150	BETA <- -> LIQUID	TRANSITION
1100	39.463	102.418	72.824	30.581	0.	0.
1200	39.463	105.852	75.435	32.554	0.	0.
1300	39.463	109.010	77.898	36.500	0.	0.
1400	39.463	111.935	80.226	40.446	0.	0.
1500	39.463	114.658	82.432	44.399	0.	0.
1600	39.463	117.204	84.526	48.339	0.	0.
1685.492	39.463	119.259	86.236	52.285	0.	0.
1685.492	20.834	200.650	86.236	55.659	LIQUID <- -> IDEAL GAS	FUGACITY = 1 bar
1700	20.839	200.829	87.214	59.232	0.	0.
1800	20.882	202.021	93.559	62.844	0.	0.
1900	20.949	203.152	99.297	66.500	0.	0.
2000	21.049	204.229	104.517	70.207	0.	0.
2100	21.191	205.259	109.290	73.963	0.	0.
2200	21.383	206.249	113.675	77.767	0.	0.
2300	21.636	207.205	117.721	81.617	0.	0.
2400	21.959	208.132	121.469	85.511	0.	0.
2500	22.361	209.036	124.953	89.449	0.	0.
2600	22.849	209.923	128.204	93.432	0.	0.
2700	23.430	210.796	131.247	97.460	0.	0.
2800	24.109	211.660	134.104	101.542	0.	0.
2900	24.889	212.519	136.793	105.678	0.	0.
3000	25.770	213.377	139.331	109.869	0.	0.
3100	26.753	214.238	141.734	114.115	0.	0.
3200	27.834	215.104	144.013	118.417	0.	0.
3300	29.008	215.978	146.181	122.775	0.	0.
3400	30.270	216.863	148.246	127.189	0.	0.
3500	31.611	217.759	150.220	131.659	0.	0.
3600	33.022	218.670	152.108	136.185	0.	0.
3700	34.493	219.594	153.920	140.767	0.	0.
3800	36.011	220.534	155.660	145.405	0.	0.
3900	37.585	221.490	157.336	150.099	0.	0.
4000	39.142	222.461	158.952	154.854	0.	0.
4100	40.730	223.447	160.513	159.667	0.	0.
4200	42.304	224.446	162.023	164.539	0.	0.
4300	43.874	225.460	163.487	169.471	0.	0.
4400	45.418	226.486	164.907	174.463	0.	0.
4500	46.927	227.524	166.287	179.515	0.	0.
4600	48.414	228.576	167.628	184.628	0.	0.
4700	49.884	229.608	168.936	189.802	0.	0.
4800	50.884	230.665	170.211	195.037	0.	0.
4900	52.114	231.727	171.455	200.332	0.	0.
5000	53.254	232.791	172.671	205.687	0.	0.
5200	55.250	234.914	175.024	216.202	0.	0.
5400	56.945	237.032	177.282	226.777	0.	0.
5600	58.296	239.129	179.453	237.412	0.	0.
5800	59.317	241.193	181.547	248.107	0.	0.
6000	59.709	243.172	183.564	258.862	0.	0.

PREVIOUS: December 1970 (1 atm)

CURRENT: September 1983 (1 bar)

Strontium (Sr)

Sr₁(ref)